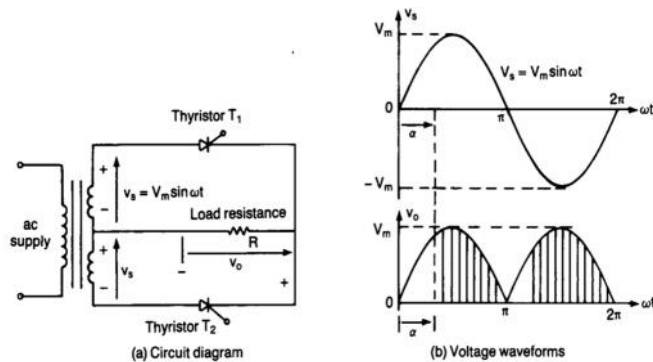


Ac-dc converters (controlled rectifiers)

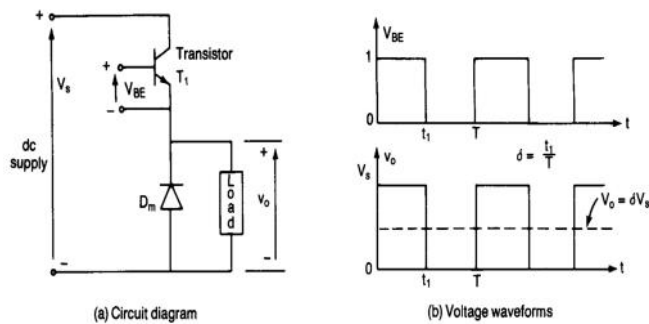
- A **single-phase** converter with two natural commutated thyristor is shown
- Average value of the output voltage can be controlled by varying the conduction time of thyristors
- This converters are also known as *controlled rectifiers*



5

Dc-dc converters (dc choppers)

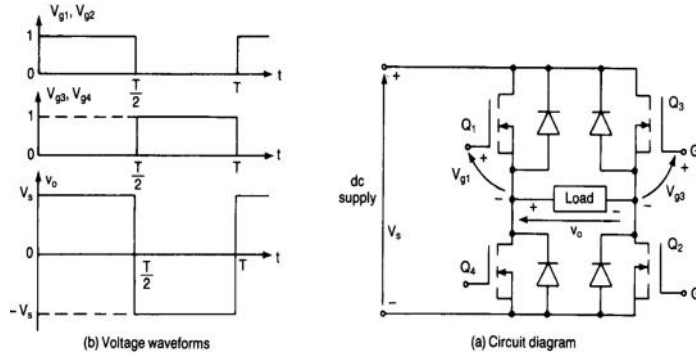
- Is also known as *Chopper or Switching Regulator*
- The average output voltage is controlled by varying the conduction of transistor, t_1 .
- If T is the chopping period, then $t_1 = \delta T$
- δ is called as the duty cycle of chopper



6

DC-AC Converters

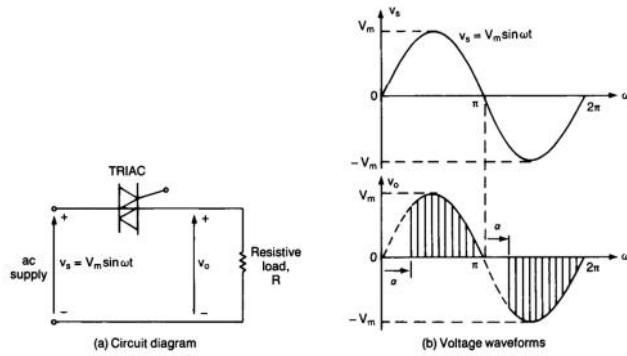
- Is also known as **Inverter**
- If transistor Q1 and Q2 conduct for one-half period and Q3 and Q4 conduct the other half, the output voltage is of alternating form
- Fixed dc voltage to variable ac voltage
- Voltage control is obtained by controlling duty cycle
- Also known as inverter



7

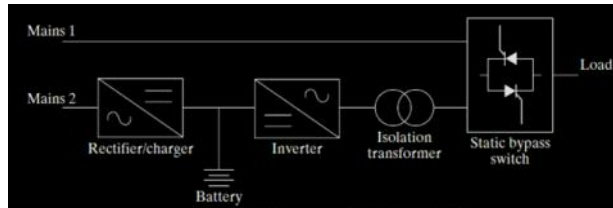
AC-AC Converters

- AC Voltage Controller / Cyclo Converter
- **Fixed AC source into variable AC** output voltage
- a single-phase converter with a TRIAC is shown below



Static Switches

- Power devices can be operated as static switches or contactors
- Supply to these switches could be either AC or DC
- **The switches are called as AC static switches or DC switches**
- Power electronic devices used as static switches in an UPS shown
- Mains 1 and 2 are connected to same supply
- Mains 1 supplies the load thro static bypass switch
- The rectifier charges the battery from Mains 2.
- The inverter supplies the emergency power to the load



CMRIT

9

1b Explain the peripheral effects of power electronic equipments.

4

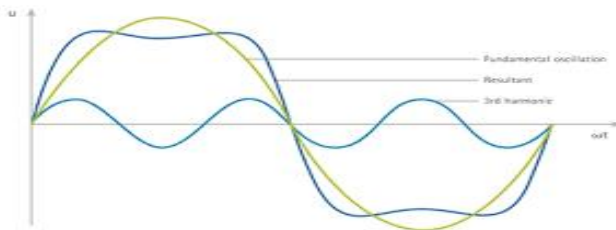
CO1

L2

Harmonics

- **Harmonics** are unwanted higher frequencies which superimposed on the fundamental waveform (50 Hz) creating a distorted wave pattern.
- **Harmonic** is a
 - voltage or current waveforms at a multiple of the fundamental frequency of the system,
 - produced by the action of non-linear loads such as rectifiers, discharge lighting, or saturated magnetic devices.
- "harmonics" are multiples of the fundamental frequency f and can therefore be expressed as: $2f$, $3f$, $4f$, etc.

12



Need for Filter

Effects of Harmonics

The operations of the power converters are based mainly on the switching of power semiconductor devices

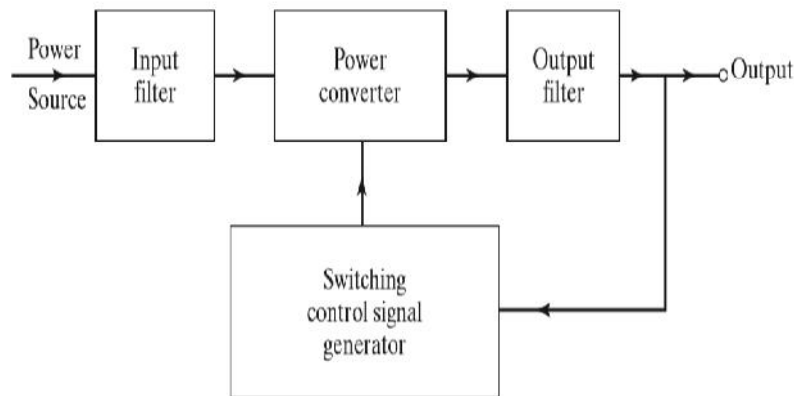
- As a result the converters **introduce current and voltage harmonics into the supply system and on the output of the converters.** These can cause
 - Problems of distortion of the output voltage and current
 - harmonic generation into the supply system
 - Interference with the communication and signalling circuits.
 - Harmonic frequencies in the power grid are a frequent cause of **power quality problems.**
 - Increased heating in the equipment and conductors
 - Misfiring in variable speed drives
 - Torque pulsations in motors.

13

Need for filter

- It is normally necessary to introduce filters on the input and output of a converter system to reduce the harmonic level to an acceptable magnitude.

Generalized Power Converter System



2a

Analyze the reverse recovery characteristics of power diode with the help of waveforms and also obtain an expression for peak reverse current.

Q2. a. Describe reverse recovery characteristics of diode. (6 marks)

Reverse Recovery Characteristics

- The current in a forward-biased junction diode is due to the net effect of majority and minority carriers.
- Once a diode is in a forward conduction mode and then its **forward current is reduced to zero (due to the natural behavior of the diode circuit or application of a reverse voltage), the diode continues to conduct due to minority carriers that remain stored in the pn-junction and the bulk semiconductor material.**
- The minority carriers require a certain time to recombine with opposite charges and to be neutralized.
- This time is called the reverse recovery time of the diode.

There are two types of recovery:

- ✓ soft recovery
- ✓ hard (or abrupt) recovery.

The soft-recovery type is more common.

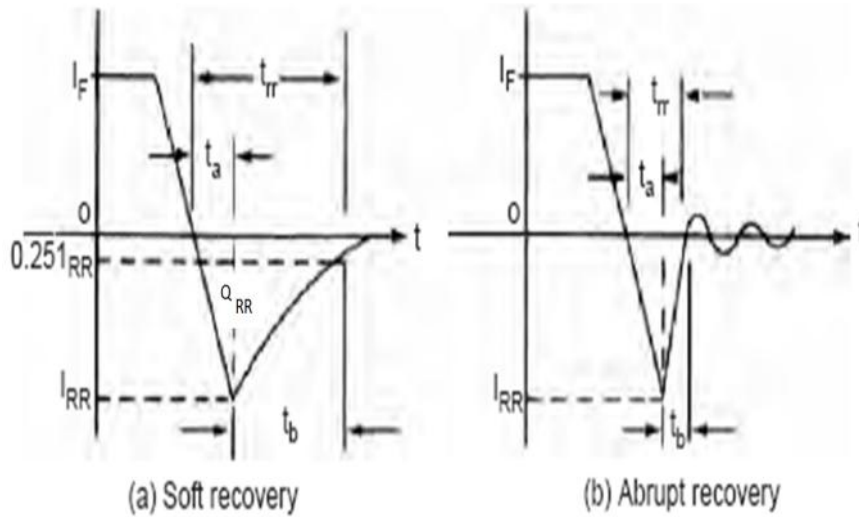
7

CO1

L3

2

Reverse Recovery Characteristics



2

The Reverse recovery time t_{rr}

- The reverse recovery time t_{rr} is measured from the initial zero crossing of the diode current to 25% of maximum (or peak) reverse current I_{RR} .
- During the changeover from forward conduction to reverse blocking condition

The t_{rr} consists of two components, t_a and t_b .

- ✓ Parameter t_a is the interval between the initial zero crossing of the diode current and peak (maximum) reverse current I_{RR} . t_a is due to charge storage in the depletion region of the junction
- ✓ Parameter t_b is the time interval between the maximum reverse recovery current to 25% of maximum (or peak) reverse current I_{RR} . The t_b is due to charge storage in the bulk semiconductor material.
- ✓ The lower t_{rr} means fast diode switching.

Softness factor $SF = t_b / t_a$

- ✓ The ratio of the two parameters t_b and t_a is known as the softness factor SF .

- Reverse Recovery time t_{rr}

$$t_{rr} = t_a + t_b$$

- Peak Reverse Current I_{RR}

$$I_{RR} = t_a \frac{di}{dt}$$

- Reverse Recovery Charge Q_{RR}

$$Q_{RR} = Q_1 + Q_2 \cong \frac{1}{2} I_{RR} t_a + \frac{1}{2} I_{RR} t_b = \frac{1}{2} I_{RR} t_{rr} \quad \text{or} \quad I_{RR} \cong \frac{2Q_{RR}}{t_{rr}}$$

- ✓ Reverse Recovery Charge Q_{RR} is the amount charge carriers that flows across the diode in the reverse direction due to change over from forward conduction to reverse blocking condition.
- ✓ Its value is determined from the area enclosed by the curve of the reverse recovery current.

$$Q_{RR} = \frac{1}{2} I_{RR} t_a + \frac{1}{2} I_{RR} t_b = \frac{1}{2} I_{RR} t_{rr}$$

$$I_{RR} = \frac{2Q_{RR}}{t_{rr}} = t_a \frac{di}{dt}$$

$$t_{rr} t_a = \frac{2Q_{RR}}{di/dt}$$

t_b is negligible compared to t_a $t_{rr}^2 = \frac{2Q_{RR}}{di/dt}$
 t_a

$$t_{rr} \cong \sqrt{\frac{2Q_{RR}}{di/dt}}$$

$$I_{RR} = \sqrt{2Q_{RR} \frac{di}{dt}}$$

3

2b The reverse recovery time of a diode is $5\mu\text{s}$ and rate of fall of the diode current is $100\text{A}/\mu\text{s}$. Determine (i) Storage charge Q_{RR} (ii) Peak reverse current I_{RR}

Given Data

Reverse recovery time of a diode $t_{rr} = 5\mu\text{s}$

Rate of fall of the diode current $di/dt = 100\text{A}/\mu\text{s}$

1. To find QRR

$$Q_{RR} = \frac{1}{2} \frac{di}{dt} t_{rr}^2$$

$$Q_{RR} = \frac{1}{2} \frac{100}{10^{-6}} (5 * 10^{-6})^2 = 1250 \mu\text{c}$$

3

CO1

L3

1

1

2. Peak reverse current IRR

$$I_{RR} = \sqrt{2Q_{RR} \frac{di}{dt}}$$

$$IRR = \sqrt{2 * 1250 * 10^{-6} * \frac{100}{10^{-6}}}$$

IRR = 500 A

1

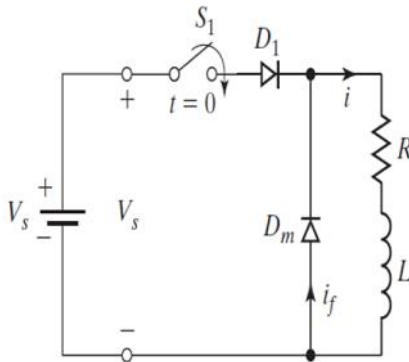
3 Explain the function of a freewheeling diode in a switched RL load with the help of circuit diagram and waveforms.

10

CO1

L2

Freewheeling diodes with RL Load

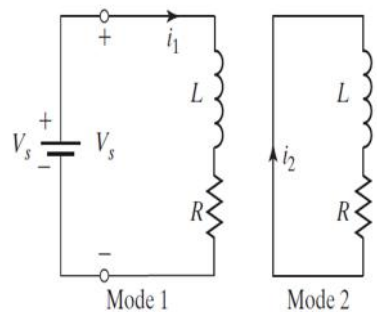


(a) Circuit diagram

D1 – Normal Diode
Dm – Freewheeling Diode

- If switch S_1 is closed for time t_1 , a current is established through the load;
- If the switch is opened, a path must be provided for the current in the inductive load.
- Otherwise, the inductive energy induces a very high voltage and this energy is dissipated as heat across the switch as sparks.
- This is normally done by connecting a diode D_m as shown in Figure, and this diode is usually called a *freewheeling diode*.
- Diode D_m is needed to provide a path for the inductive load current.
- Diode D_1 is connected in series with the switch and it will prevent any negative current flow through the switch if there is an ac input supply voltage.
- But for dc supply, there is no need for D_1 .

2



(b) Equivalent circuits

- The circuit operation can be divided into **Two modes**.
- Mode 1 begins when the switch is closed at $t = 0$
- Mode 2 begins when the switch is opened.
- The equivalent circuits for the modes are shown in Figure.
- Variables i_1 and i_2 are defined as the instantaneous currents for mode 1 and mode 2, respectively;
- t_1 and t_2 are the corresponding durations of these modes.

2

Mode 1

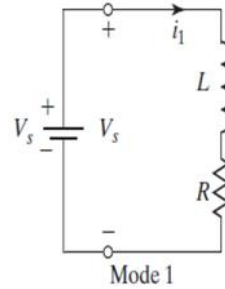
- Diode current i_1

$$i_1(t) = \frac{V_s}{R} (1 - e^{-tR/L})$$

- When the switch is opened at $t = t_1$ (at the end of this mode),
- Diode current i_1 at $t = t_1$ becomes

$$I_1 = i_1(t = t_1) = \frac{V_s}{R} (1 - e^{-t_1R/L})$$

- If the time t_1 is sufficiently long, the current practically reaches a **steady-state current of $I_s = V_s/R$** flows through the load.



2

Mode 2

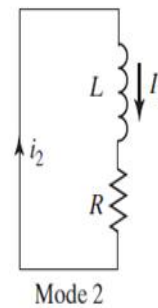
- This mode begins when the **switch is opened and the load current starts to flow through the freewheeling diode D_m** .
- Redefining the time origin at the beginning of this mode, the differential equation for the freewheeling diode is found f

$$0 = L \frac{di_2}{dt} + Ri_2$$

- with initial condition $i_2(t = t_1) = I_1$.
- the free i_2 is given by

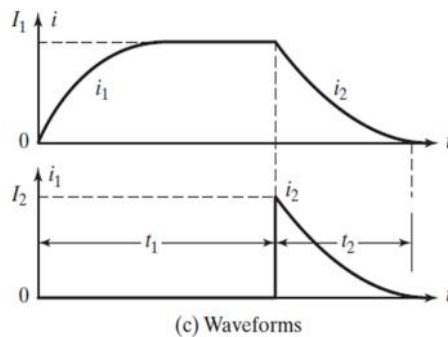
$$i_2(t) = I_1 e^{-tR/L}$$

- at $t = t_2$ this current decays exponentially to practically zero provided that $t_2 > L/R$.



2

Waveforms of Currents



2

4

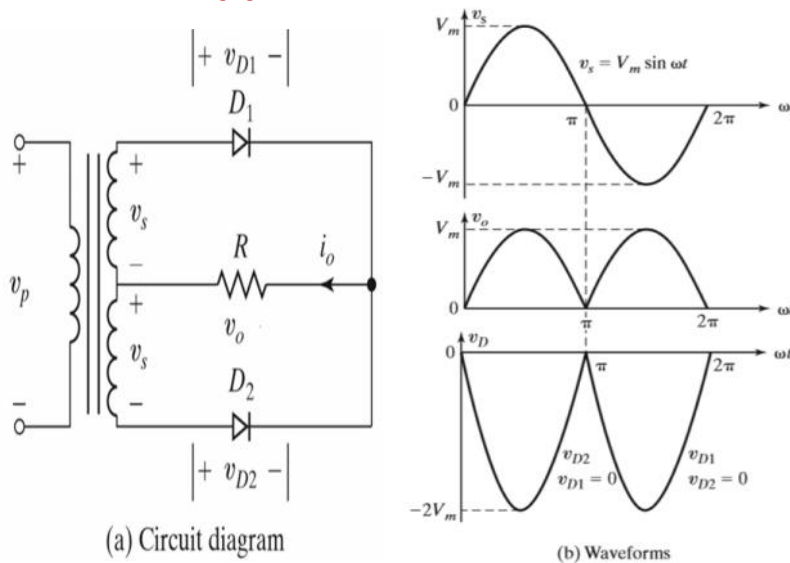
A single-phase full-wave rectifier with center-tapped transformer has a purely resistive load of R , Determine (a) Average voltage and current (b) RMS voltage and current (c) dc output power (d) ac output power (e) the efficiency (f) Ripple factor (g) Form Factor (h) TUF (i) the input power factor PF, (j) CF of the input current.

10

CO1

L3

Center-tapped Full wave Rectifier



1

During the positive half-cycle of the input voltage

- Diode D_1 conducts and diode D_2 is in a blocking condition.
- The input voltage appears across the load.

During the negative half-cycle of the input voltage

- Diode D_2 conducts while diode D_1 is in a blocking condition.
- The negative portion of the input voltage appears across the load as a positive voltage.
- The peak inverse voltage of a diode is $2V_m$
- PIV of diode, $D_2 = V_m + V_m$

Performance Parameters for Full wave Rectifier

1. Average value of the output voltage, V_{dc}

$$V_{dc} = \frac{2}{T} \int_0^{T/2} V_m \sin \omega t dt \quad T = 2\pi$$

$$V_{dc} = \frac{1}{\pi} \int_0^{\pi} V_m \sin \omega t d\omega t :$$

$$= \frac{V_m}{\pi} (-\cos \omega t) \Big|_0^{\pi}$$

$$= \frac{V_m}{\pi} (-\cos \pi + \cos 0^\circ)$$

$$V_{dc} = \frac{2V_m}{\pi} = 0.6366V_m$$

2. Average value of the output current (Load), I_{dc}

$$I_{dc} = \frac{V_{dc}}{R} = \frac{0.6366V_m}{R}$$

3. Output dc power, P_{dc}

$$P_{dc} = V_{dc} I_{dc}$$

$$P_{dc} = (0.6366V_m)^2/R$$

4. RMS value of the output voltage, V_{rms}

$$V_{rms} = \left[\frac{2}{T} \int_0^{T/2} (V_m \sin \omega t)^2 dt \right]^{1/2}$$

$$T = 2\pi$$

The rms value of the load voltage V_{rms} can be calculated as follows:

$$\begin{aligned} V_{rms} &= \sqrt{\frac{1}{\pi} \int_0^{\pi} v_s^2(\omega t) d\omega t} \\ &= \sqrt{\frac{1}{\pi} \int_0^{\pi} (V_m \sin \omega t)^2 d\omega t} \\ &= \sqrt{\frac{(V_m)^2}{\pi} \int_0^{\pi} \frac{1}{2} (1 - \cos 2\omega t) d\omega t} = \frac{V_m}{\sqrt{2}} \\ V_{rms} &= \frac{V_m}{\sqrt{2}} = 0.707V_m \end{aligned}$$

5. RMS value of the output Current, I_{rms}

$$I_{rms} = \frac{V_{rms}}{R} = \frac{0.707V_m}{R}$$

6. Output ac power, P_{ac}

$$P_{ac} = V_{rms} I_{rms}$$

$$P_{ac} = (0.707V_m)^2 / R.$$

7. Efficiency, η (Rectification Ratio)

$$\eta = P_{dc}/P_{ac}$$

$$\text{efficiency } \eta = (0.6366V_m)^2/(0.707V_m)^2 = 81\%.$$

1

8. AC component of Output Voltage

Output voltage consists of 1. DC component 2. AC component

$$V_{ac} = \sqrt{V_{rms}^2 - V_{dc}^2}$$

9. Form factor, FF – Measure of the shape of the output voltage

$$FF = \frac{V_{rms}}{V_{dc}}$$

$$FF = 0.707V_m/0.6366V_m = 1.11.$$

1

10. Ripple factor, RF – Measure of Ripple content

$$RF = \frac{V_{ac}}{V_{dc}} \quad V_{ac} = \sqrt{V_{rms}^2 - V_{dc}^2}$$

$$RF = \sqrt{\left(\frac{V_{rms}}{V_{dc}}\right)^2 - 1} = \sqrt{FF^2 - 1}$$

$$RF = \sqrt{1.11^2 - 1} = 0.482 \text{ or } 48.2\%.$$

1

11. Peak Inverse Voltage

Center tapped Full wave Rectifier : $2 V_m$

Bridge type Full wave Rectifier : V_m

1

12. Transformer utilization factor, TUF

- TUF indicates how effectively the transformer capacity is used in delivering dc power to load for a given ac power.
- It is the ratio of dc power delivered to the load to ac power rating of secondary winding of the transformer.
- $TUF = P_{dc}/V_s I_s = P_{dc}/V_{rms} I_{rms}$ (transformer secondary)
- V_s, I_s are rms voltage and current of the transformer secondary
- TUF for Center tapped full wave rectifier = 0.693 = 69.3%
- TUF for bridge type full wave rectifier = 0.812 = 81.2%

2

Transformer Utilization Factor (TUF) of center-tapped Full Wave Rectifier

$$TUF = \frac{P_{dc}}{V_s I_s}$$
$$P_{dc} = V_{dc} I_{dc} = \frac{2V_m}{\pi} \cdot \frac{2I_m}{\pi}$$
$$P_{dc} = \frac{4V_m I_m}{\pi^2}$$

VA Rating of Transformer Secondary

$$V_s I_s = V_{rms} \cdot I_{rms}$$
$$V_{rms} = \frac{V_m}{\sqrt{2}}$$
$$I_{rms} = \frac{I_m}{\sqrt{2}}$$
$$V_s I_s = \frac{2 \times V_m}{\sqrt{2}} \cdot \frac{I_m}{\sqrt{2}}$$
$$V_s I_s = \frac{V_m I_m}{\sqrt{2}}$$

$$TUF \text{ WRT secondary} = \frac{P_{dc}}{V_s I_s} = \frac{4V_m I_m}{\pi^2} \times \frac{\sqrt{2}}{V_m I_m}$$
$$= 0.5732$$
$$TUF = \frac{0.8106 + 0.5732}{2} = 0.693 = 69.3\%$$

Department of EEE

CMRIT

22

13. Crest Factor

Crest factor (CF), which is a measure of the peak input current $I_{s(\text{peak})}$ as compared with its rms value I_s , is often of interest to specify the peak current ratings of devices and components. CF of the input current is defined by

$$CF = \frac{I_{s(\text{peak})}}{I_s}$$

1

14. Input Power Factor

Centre Tapped Rectifier.

$$PF = \frac{P_{ac}}{V_s I_s}$$
$$= \frac{0.707^2 V_m^2 / R}{2 \times \frac{V_m}{\sqrt{2}} \times \frac{I_m}{2}}$$
$$= 0.707^2 \times \sqrt{2}$$
$$PF = 0.707 = \frac{1}{\sqrt{2}}$$

5a	<p>Explain different types of power diodes.</p> <p>Types of Power Diodes</p> <ul style="list-style-type: none"> Depending on the recovery characteristics, on state drop and manufacturing techniques, the power diodes can be classified into the following categories: <ol style="list-style-type: none"> General-purpose diodes or Standard diodes Fast-recovery diodes Schottky diodes <p>Special Diodes</p> <ol style="list-style-type: none"> Silicon Carbide Diodes Silicon Carbide Schottky Diodes Freewheeling diodes <p style="text-align: center;">1. General-Purpose Diodes (standard diodes)</p> <ul style="list-style-type: none"> General-purpose diodes are available up to 5000 V, 4500 A The general-purpose rectifier diodes have relatively high reverse recovery time t_{rr}, typically 25 μs Used in low-speed applications, where recovery time is not critical (e.g., diode rectifiers and converters for a low-input frequency up to 1-kHz applications and line-commutated converters). Current ratings from less than 1 A to several thousands of amperes Voltage ratings from 50 V to around 5 kV. These diodes are generally manufactured by diffusion. <p style="text-align: center;">1</p> <p style="text-align: center;">2. Fast-Recovery Diodes</p> <ul style="list-style-type: none"> The fast-recovery diodes have low recovery time, normally less than 5μs. They are used in dc–dc and dc–ac converter circuits, where the speed of recovery is often of critical importance. Voltage rating from 50 V to around 3 kV Current rating less than 1 A to hundreds of amperes. For voltage ratings above 400 V, fast-recovery diodes are generally made by diffusion and the recovery time is controlled by platinum or gold diffusion. For voltage ratings below 400 V, epitaxial diodes provide faster switching speeds than those of diffused diodes. The epitaxial diodes have fast recovery time of as low as 50 ns. <p style="text-align: center;">22</p>	6 3 3	CO1	L2
----	---	---------------------	-----	----

Schottky Diodes

- The charge storage problem of a pn -junction can be eliminated (or minimized) in a Schottky diode.
- It is accomplished by setting up a “barrier potential” with a contact between a metal and a semiconductor.
- A layer of metal is deposited on a thin epitaxial layer of n -type silicon.
- The rectifying action depends on the majority carriers only, and as a result there are no excess minority carriers to recombine.
- The recovery effect is due to the self capacitance of the semiconductor junction.
- The recovered charge of a Schottky diode is much less than that of an equivalent pn junction diode. Because it is due only to the junction capacitance, it is largely independent of the reverse di/dt .
- A Schottky diode has a relatively low forward voltage drop.
- The leakage current of a Schottky diode is higher than that of a pn -junction diode.
- A Schottky diode with relatively low-conduction voltage has relatively high leakage current, and vice versa.
- As a result, the maximum allowable voltage of this diode is generally limited to 100 V.
- The current ratings of Schottky diodes vary from 1 to 400 A.
- The Schottky diodes are ideal for high-current and low-voltage dc power supplies.
- However, these diodes are also used in low-current power supplies for increased efficiency.

24

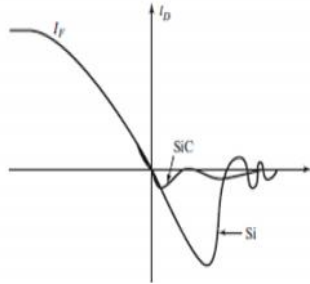
Advantages of Schottky diode

- The capacitance of the diode is low as the depletion region of the diode is negligible.
- The reverse recovery time of the diode is very fast, that is the change from ON to OFF state is fast.
- The current density of the diode is high as the depletion region is negligible.
- The turn-on voltage of the diode is 0.2 to 0.3 volts, which is very low.

25

4. Silicon Carbide Diodes

- Silicon carbide (SiC) is a new material for power electronics.
- Its physical properties outperform Silicon (Si) and Gallium Arsenide GaAs by far.
- The typical storage charge Q_{RR} is
 - ✓ 21 nC for a 600-V, 6-A diode
 - ✓ 23 nC for a 600-V, 10-A device.



- They have the following features:
 - No reverse recovery time;
 - Ultrafast switching behavior;
 - No temperature influence on the switching behavior.

27

Advantages

- Low reverse recovery current.
- SiC power devices enable increased efficiency
- Reduced size
- higher switching frequency
- produce significant less electromagnetic interference (EMI) in a variety of applications.
- silicon-carbide diodes show four times better dynamic characteristics with 15% less forward voltage (V_F) than standard silicon diodes

Applications

- power supplies, solar energy conversion, transportations, and other applications such as welding equipment and air conditioners.

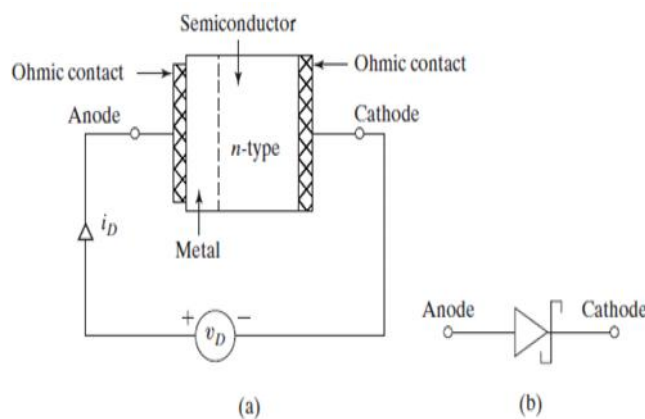
28

Features of SiC Schottky diodes

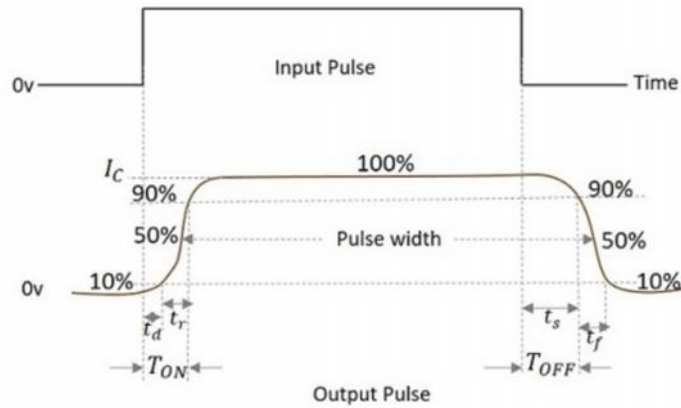
- Lowest switching losses due to low reverse recovery charge;
 - Fully surge-current stable, high reliability, and ruggedness;
 - Lower system costs due to reduced cooling requirements;
 - Higher frequency designs and increased power density solutions.
-
- These devices also have low device capacitance that enhances overall system efficiency, especially at higher switching frequencies.

30

Basic Structure of Schottky Diodes



31



- **Time delay (t_d)** – The time taken by the collector current to reach from its initial value to 10% of its final value is called as the **Time Delay**.
- **Rise time (t_r)** – The time taken for the collector current to reach from 10% of its initial value to 90% of its final value is called as the **Rise Time**.
- **Turn-on time (T_{ON})** – The sum of time delay (t_d) and rise time (t_r) is called as **Turn-on time**.

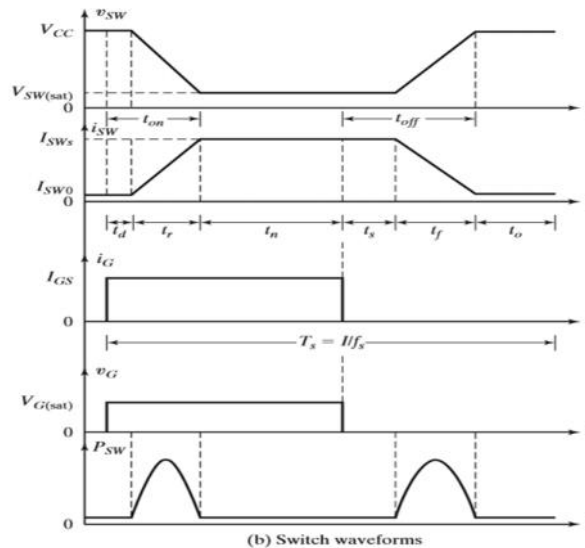
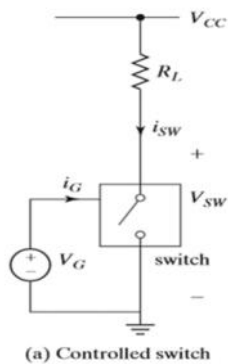
$$T_{ON} = t_d + t_r$$

- **Storage time (t_s)** – The time interval between the trailing edge of the input pulse to the 90% of the maximum value of the output, is called as the **Storage time**.
- **Fall time (t_f)** – The time taken for the collector current to reach from 90% of its maximum value to 10% of its initial value is called as the **Fall Time**.
- **Turn-off time (T_{OFF})** – The sum of storage time (t_s) and fall time (t_f) is defined as the **Turn-off time**.

$$T_{OFF} = t_s + t_f$$

- **Pulse Width (W)** – The time duration of the output pulse measured between two 50% levels of rising and falling waveform is defined as **Pulse Width**.

Characteristics of Practical Devices



6b	<p>List out the switch specifications.</p> <p>Switch Specifications</p> <ol style="list-style-type: none"> 1. Voltage ratings 2. Current ratings 3. Switching speed or frequency f_s 4. di/dt rating 5. dv/dt rating 6. Switching losses 7. Gate-drive requirements 8. Safe operating area (SOA) 9. I^2t for fusing 10. Temperatures 11. Thermal resistance 	4	CO1	L1
7a	<p>With circuit diagram and waveforms, explain uncontrolled single-phase bridge type full wave rectifier with R load.</p> <div style="text-align: center;"> </div> <p>During the positive half-cycle of the input voltage</p> <ul style="list-style-type: none"> • Diodes D1 and D2 forward biased and conduct. • Diodes D3 and D4 reverse biased • Output current flows from V_{s+}, D1, R load, D2, V_{s-} <p>During the negative cycle of the input voltage</p> <ul style="list-style-type: none"> • Diodes D3 and D4 forward biased and conduct. • Diodes D1 and D2 reverse biased. • Output current flows from V_{s+}, D3, R load, D4, V_{s-} ➤ The peak inverse voltage of a diode is only V_m. ➤ This circuit is known as a bridge rectifier ➤ It is commonly used in industrial applications 	5	CO1	L2
7b	<p>Compare the advantages and disadvantages of bridge rectifier and rectifier with center tapped transformer.</p>	5	CO1	L2

Advantages and Disadvantages of Center-Tapped and Bridge Rectifiers

	Advantages	Disadvantages
Center-tapped transformer	<ul style="list-style-type: none"> Simple, only two diodes Ripple frequency is twice the supply frequency Provides an electrical isolation 	<ul style="list-style-type: none"> Limited low power supply, less than 100 W Increased cost due to the center-tapped transformer Dc current flowing through each side of the secondary will increase the transformer cost and size
Bridge rectifier	<ul style="list-style-type: none"> Suitable for industrial applications up to 100 kW Ripple frequency is twice the supply frequency Simple to use in commercially available units 	<ul style="list-style-type: none"> The load cannot be grounded without an input-side transformer Although an input-side transformer is not needed for the operation of the rectifier, one is normally connected to isolate the load electrically from the supply